



PSMN9R8-30MLC

N-channel 30 V 9.8 m Ω logic level MOSFET in LPAK33 using NextPower Technology

Rev. 3 — 15 June 2012

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching
- Synchronous buck regulator

1.4 Quick reference data

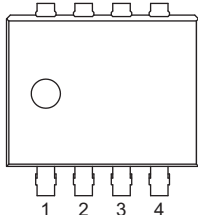
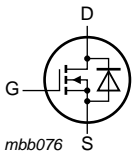
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see Figure 1	-	-	50	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	45	W
T _j	junction temperature		-55	-	175	°C
Static characteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C; see Figure 10	-	10.65	12.4	m Ω
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see Figure 10	-	8.5	9.8	m Ω
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 4.5 V; I _D = 15 A; V _{DS} = 15 V; see Figure 12 ; see Figure 13	-	1.5	-	nC
Q _{G(tot)}	total gate charge	V _{GS} = 4.5 V; I _D = 15 A; V _{DS} = 15 V; see Figure 12 ; see Figure 13	-	5	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT1210 (LFAK33)

3. Ordering information

Table 3. Ordering information

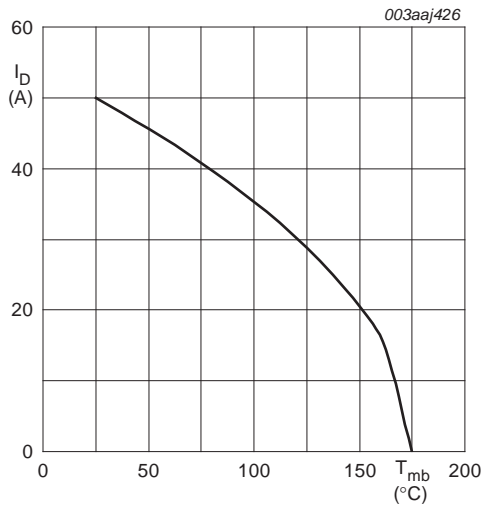
Type number	Package		Version
	Name	Description	
PSMN9R8-30MLC	LFAK33	Plastic single ended surface mounted package (LFAK33); 4 leads	SOT1210

4. Limiting values

Table 4. Limiting values

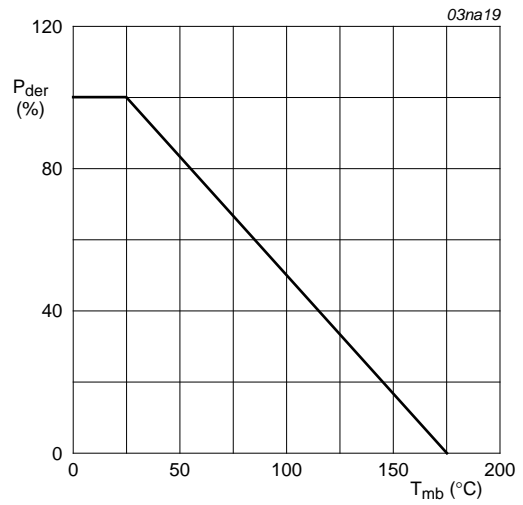
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$; see Figure 1	-	50	A
		$V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$; see Figure 1	-	36	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; see Figure 4	-	202	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	45	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	140	-	V
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	41	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	202	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ °C}; I_D = 50\text{ A}; V_{sup} \leq 30\text{ V}; R_{GS} = 50\text{ }\Omega$; unclamped; see Figure 3	-	8	mJ



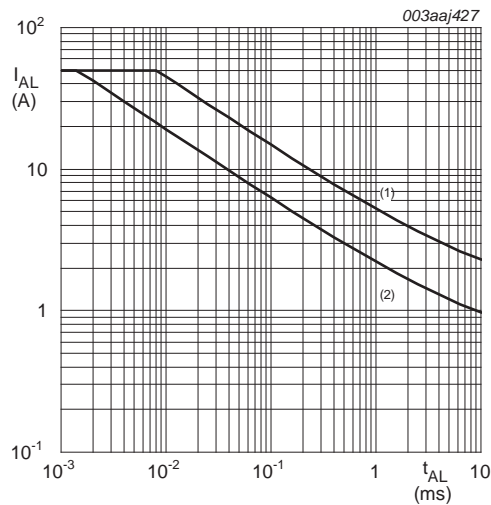
$$V_{GS} \geq 10V$$

Fig. 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{Tot}}{P_{Tot(25^\circ C)}} \times 100\%$$

Fig. 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j(0.1s)} = 25^\circ C$; (2) $T_{j(0.1s)} = 100^\circ C$

Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

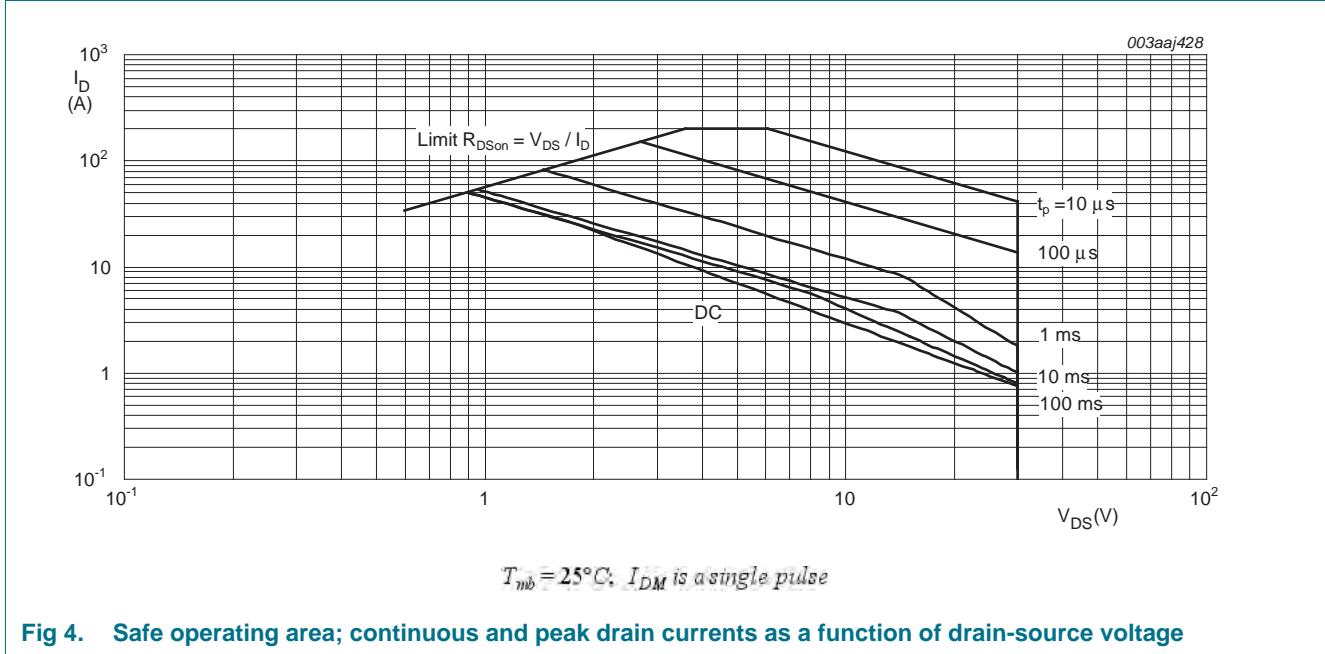


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	3.1	3.32	K/W

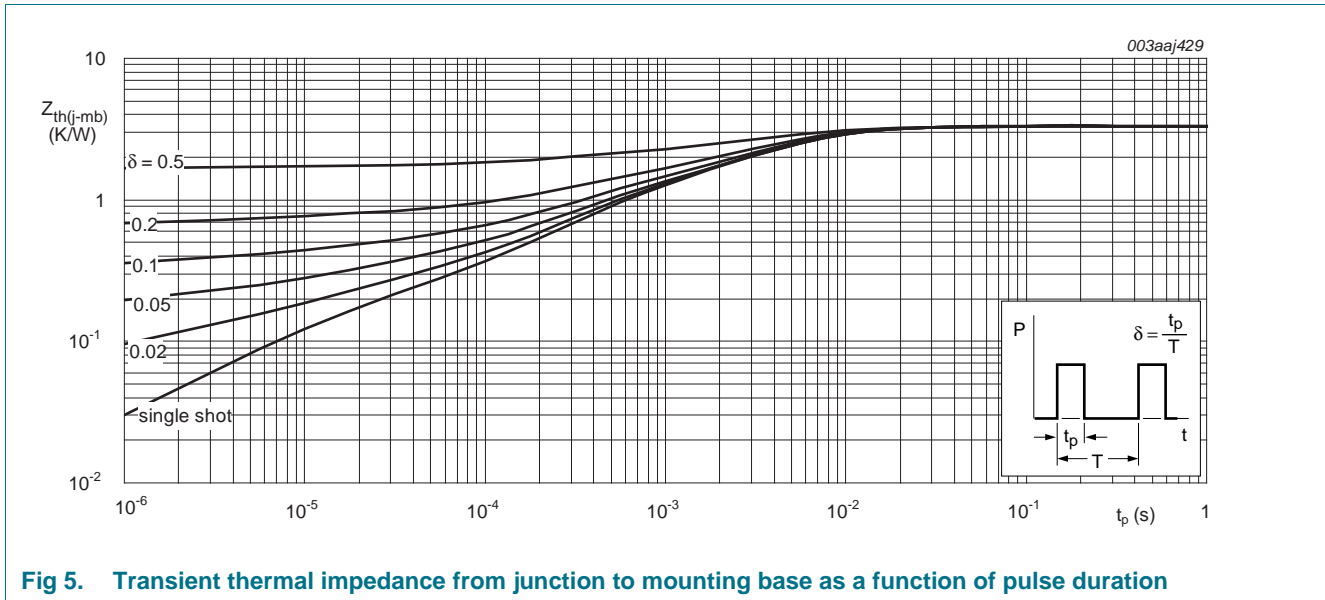


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

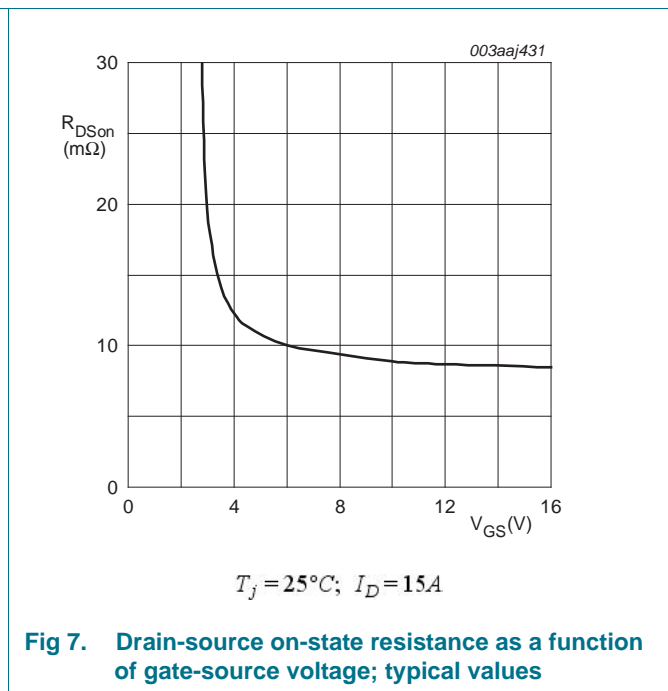
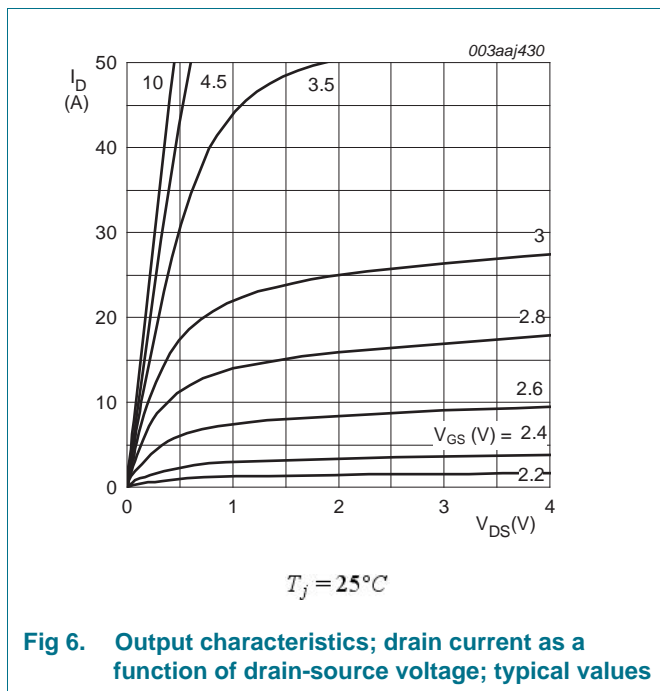
6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.3	1.64	1.95	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature		-	-4	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ }^\circ C$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C$; see Figure 10	-	10.65	12.4	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ }^\circ C$; see Figure 11 ; see Figure 10	-	-	21.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C$; see Figure 10	-	8.5	9.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ }^\circ C$; see Figure 11 ; see Figure 10	-	-	16.75	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	0.9	1.8	3.6	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V}$; see Figure 12 ; see Figure 13	-	10.9	-	nC
		$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V}$; see Figure 12 ; see Figure 13	-	5	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	10	-	nC
Q_{GS}	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V}$; see Figure 12 ; see Figure 13	-	2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.8	-	nC
Q_{GD}	gate-drain charge		-	1.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}$; see Figure 12 ; see Figure 13	-	3.1	-	V
C_{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ C$; see Figure 14	-	690	-	pF
C_{oss}	output capacitance		-	170	-	pF
C_{rss}	reverse transfer capacitance		-	52	-	pF

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 1\ \Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 5\ \Omega$	-	7.4	-	ns
t_r	rise time		-	7.7	-	ns
$t_{d(off)}$	turn-off delay time		-	11.7	-	ns
t_f	fall time		-	5.3	-	ns
Q_{oss}	output charge	$V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C}$	-	4.9	-	nC
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see Figure 15	-	0.84	1.1	V
t_{rr}	reverse recovery time	$I_S = 15\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	12.9	-	ns
Q_r	recovered charge	$V_{DS} = 15\text{ V}$	-	5.3	-	nC
t_a	reverse recovery rise time	$V_{GS} = 0\text{ V}; I_S = 15\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s};$ $V_{DS} = 15\text{ V};$ see Figure 16	-	7.9	-	ns
t_b	reverse recovery fall time		-	5	-	ns



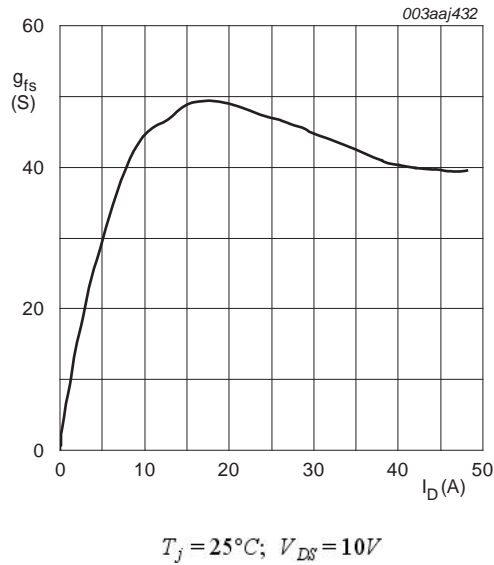


Fig 8. Forward transconductance as a function of drain current; typical values

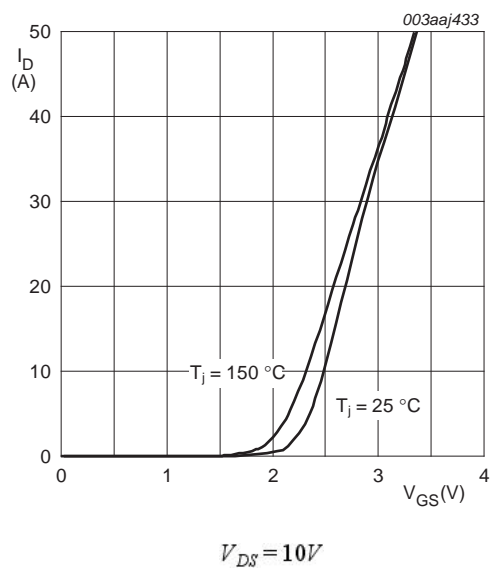


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

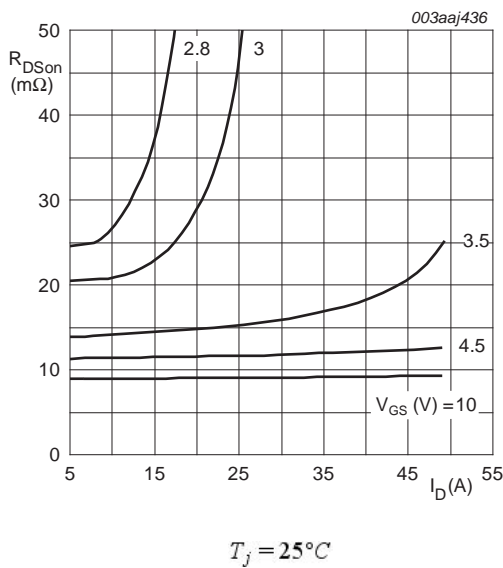


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

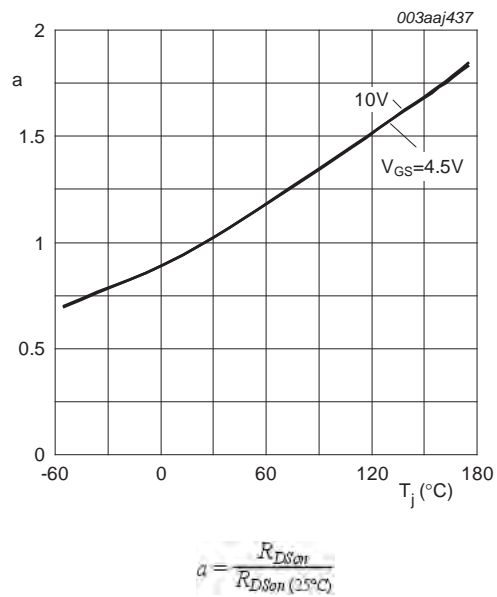


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

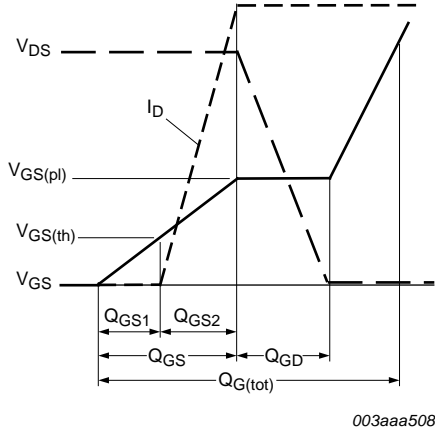
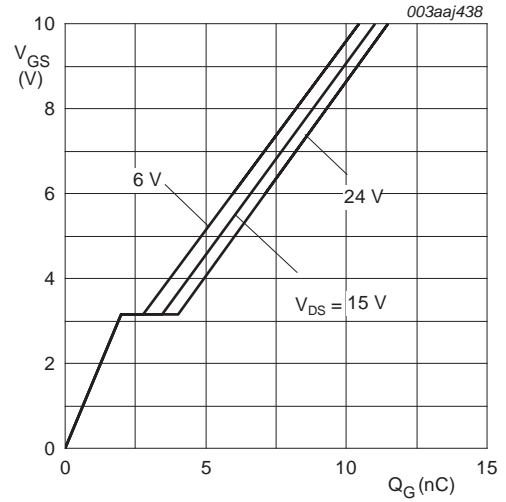
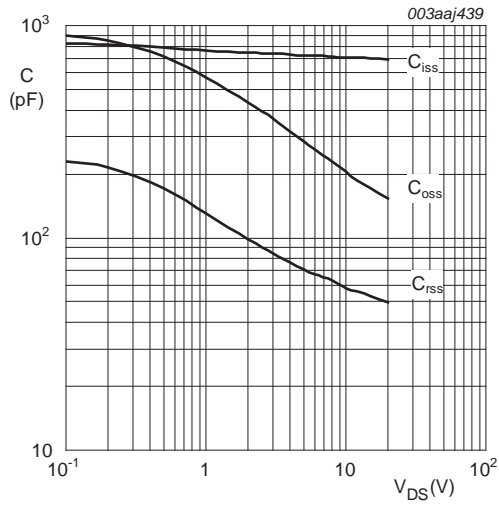


Fig 12. Gate charge waveform definitions



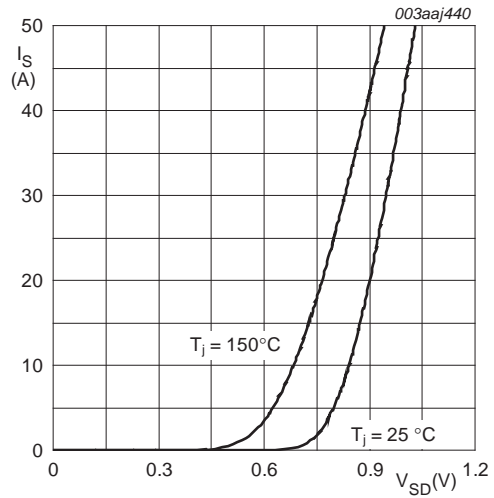
$T_j = 25^\circ\text{C}; I_D = 15\text{A}$

Fig 13. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{V}$

Fig 15. Source current as a function of source-drain voltage; typical values

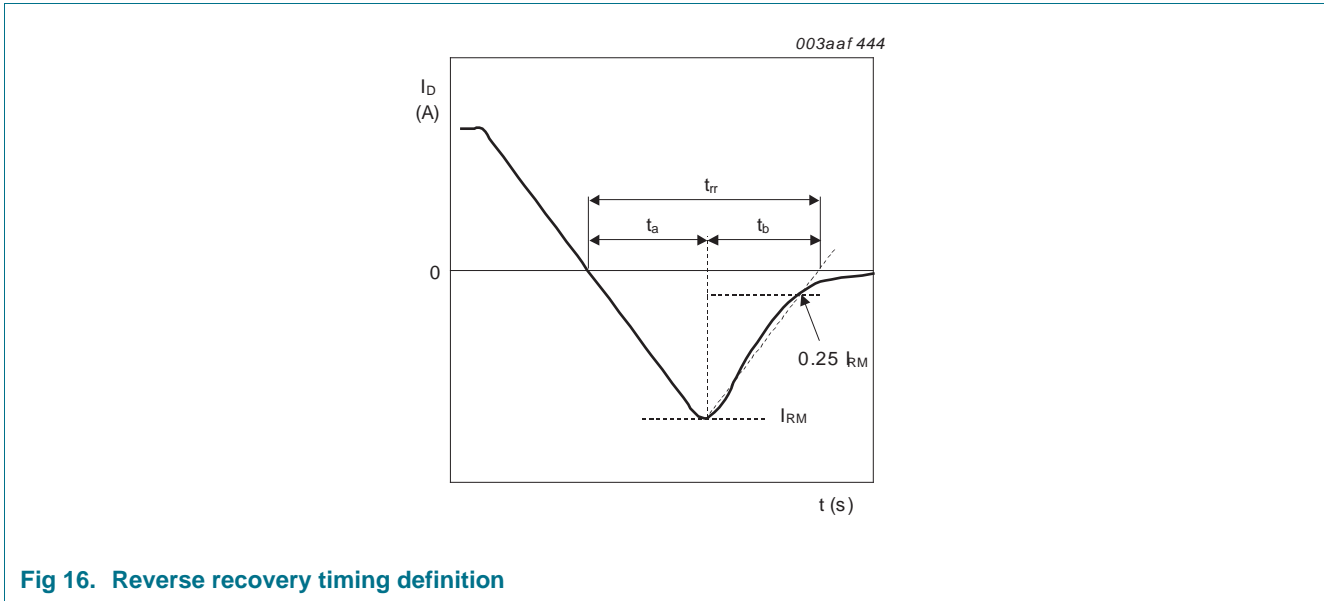


Fig 16. Reverse recovery timing definition

7. Package outline

Plastic single ended surface mounted package (LPAK33); 8 leads

SOT1210

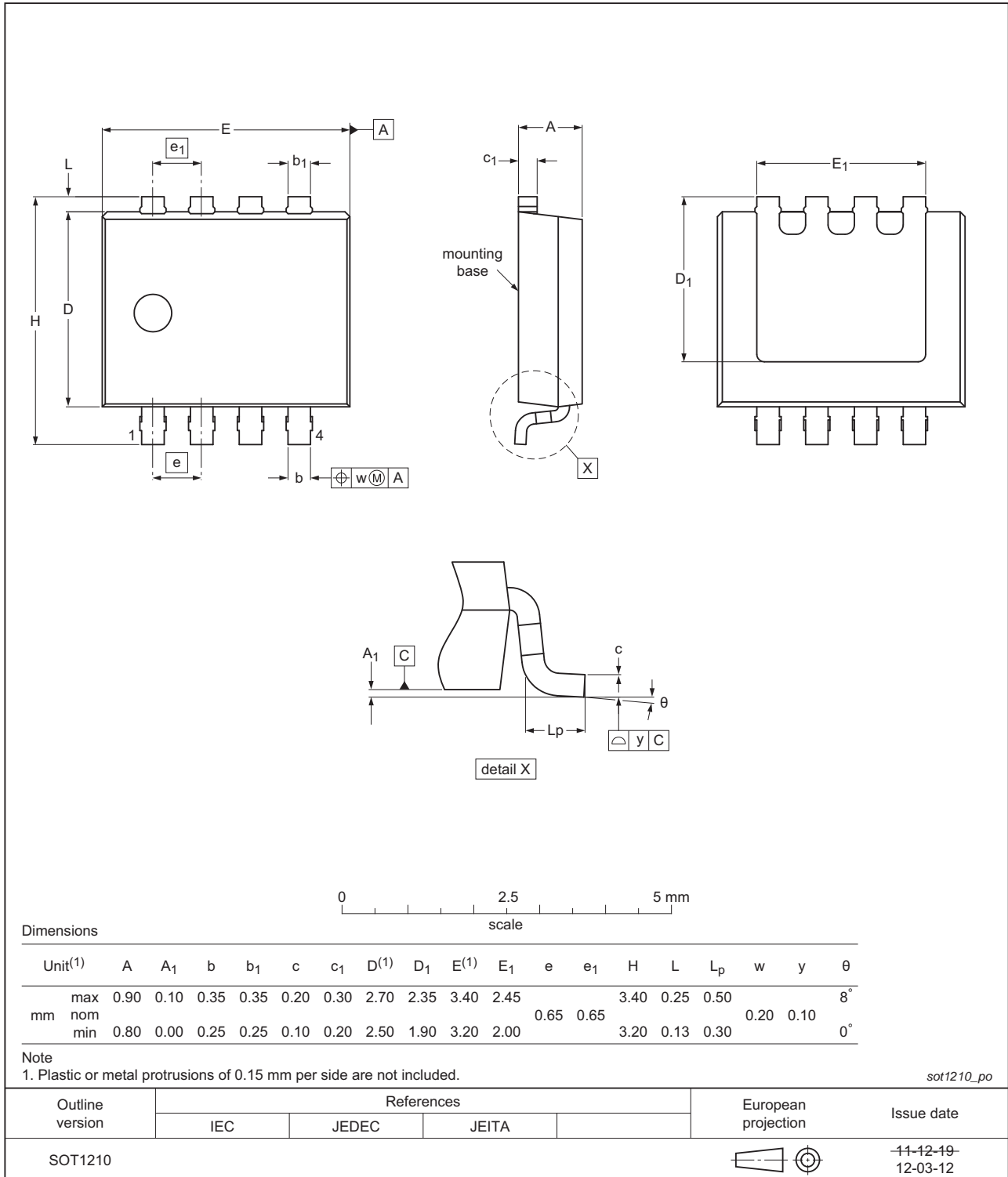


Fig 17. Package outline SOT1210 (LPAK33)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R8-30MLC v.3	20120615	Product data sheet	-	PSMN9R8-30MLC v.2
Modifications:	<ul style="list-style-type: none">• Status changed from objective to product.• Various changes to content.			
PSMN9R8-30MLC v.2	20120607	Objective data sheet	-	PSMN9R8-30MLC v.1

9. Legal information

9.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 15 June 2012
 Document identifier: PSMN9R8-30MLC